

## 60A 650V Fast recovery diode

### 1 Description

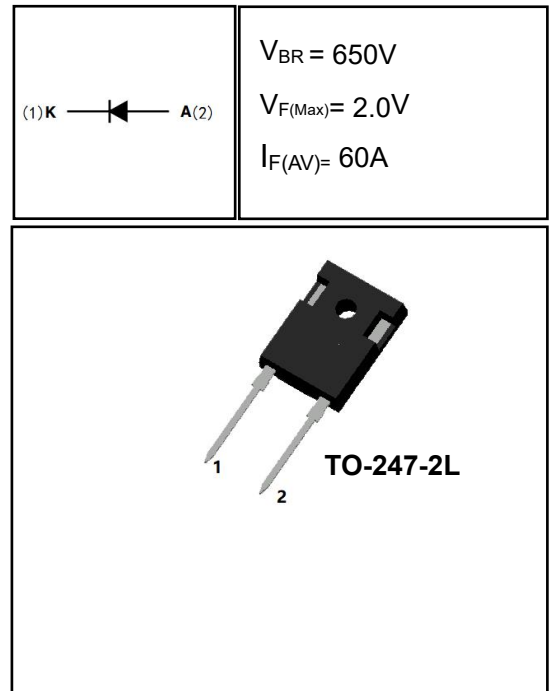
60A, 650V Ultrafast Diodes They have a low forward voltage drop and are of planar, silicon nitride passivated, ion-implanted, epitaxial construction. These devices are intended for use as energy steering/clamping diodes and rectifiers in a variety of switching power supplies and other power switching applications. Their low stored charge and ultrafast recovery with soft recovery characteristics minimizes ringing and electrical noise in many power switching circuits, thus reducing power loss in the switching transistor

### 2 Features

- Low power loss,
- high efficiency Low forward voltage,
- high current capability High surge capacity
- Super fast recovery times
- high voltage

### 3 Applications

- Switching Power Supply
- Power Switching Circuits
- General Purpose



## 4 Electrical Characteristics

### 4.1 Absolute Maximum Ratings (Tc=25°C, unless otherwise noted)

PARAMETER		SYMBOL	VALUE	UNIT
Peak Repetitive Reverse Voltage		$V_{RRM}$	650	V
Working Peak Reverse Voltage		$V_{RWM}$	650	V
DC Blocking Voltage		$V_R$	650	V
Average Rectified Forward Current	Tc=125°C	$I_{F(AV)}$	60	A
Repetitive Peak Surge Current		$I_{FRM}$	90	A
Nonrepetitive Peak Surge Current	t=8.3ms	$I_{FSM}$	550	A
Avalanche Energy(single)	L=1mH	$E_{AS}$	110	mJ
Operating Junction Temperature Range		$T_j$	-55~175	°C
Storage Temperature Range		$T_{stg}$	-55~175	°C

### 4.2 Thermal Characteristics

PARAMETER	SYMBOL	VALUE	UNIT
Thermal Resistance, Junction to Case-sink	$R_{thJC}$	0.95	°C/W

4.3 Electrical Characteristics (Tc=25°C, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
Maximum Instantaneous Forward Voltage	V <sub>F</sub>	I <sub>F</sub> = 40A	-	1.51	-	V
		I <sub>F</sub> = 50A	-	1.58	-	V
		I <sub>F</sub> = 60A	-	1.65	2.0	V
		I <sub>F</sub> = 60A, T <sub>C</sub> = 150°C	-	-	1.8	V
Maximum Instantaneous Reverse	I <sub>R</sub>	V <sub>R</sub> = 650V	-	-	5	uA
		V <sub>R</sub> = 650V, T <sub>C</sub> = 150°C	-	-	1	mA
Maximum Reverse Recovery Time	t <sub>rr</sub>	IF = 0.5A, IR=1A, IRR = 0.25A	-	36	50	ns
		V <sub>R</sub> =30V I <sub>F</sub> =1A -di/dt=200A/us	-	35	50	ns
Maximum Reverse Recovery Time	t <sub>rr</sub>	V <sub>R</sub> =300V, I <sub>F</sub> =50A, -di/dt=200A/us	-	82	-	ns
Maximum Reverse Recovery Current	I <sub>RRM</sub>		-	8	-	A
Reverse Recovery Charge	Q <sub>RR</sub>		-	287	-	nC
Total capacitance	C <sub>tot</sub>	V <sub>R</sub> =0V f=1MHz	-	600	-	pF
DC Blocking Voltage	V <sub>BR</sub>	I <sub>R</sub> =100uA	650	710	-	V

DEFINITIONS

V<sub>F</sub> = Instantaneous forward voltage (pw = 300µs, D = 2%).

I<sub>R</sub> = Instantaneous reverse current.

RθJC = Thermal resistance junction to case.

pw = pulse width.

D = duty cycle.

5 Typical characteristics diagrams

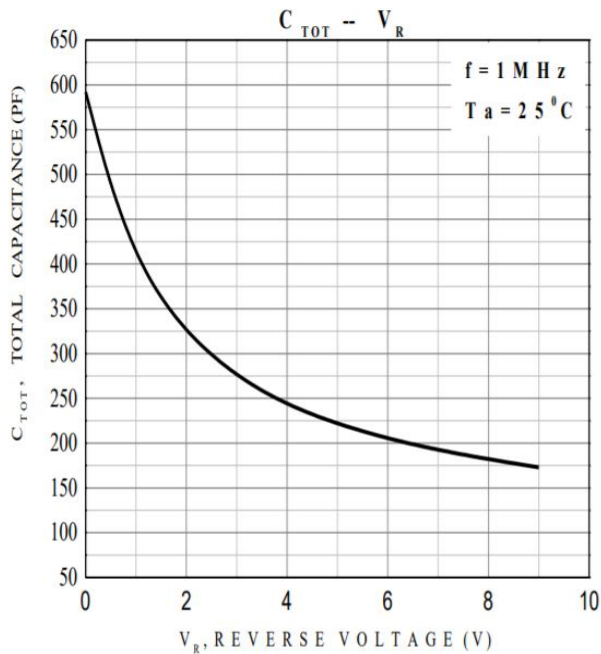


FIGURE 1. Total capacitance vs Voltage

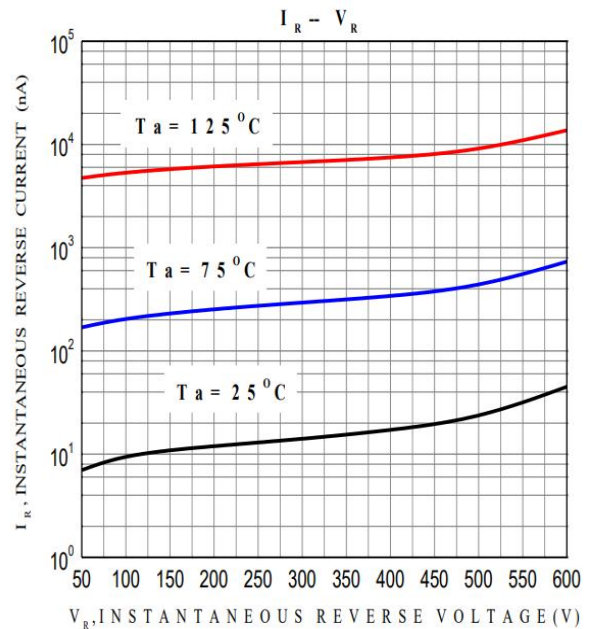


FIGURE 2. REVERSE CURRENT vs REVERSE VOLTAGE

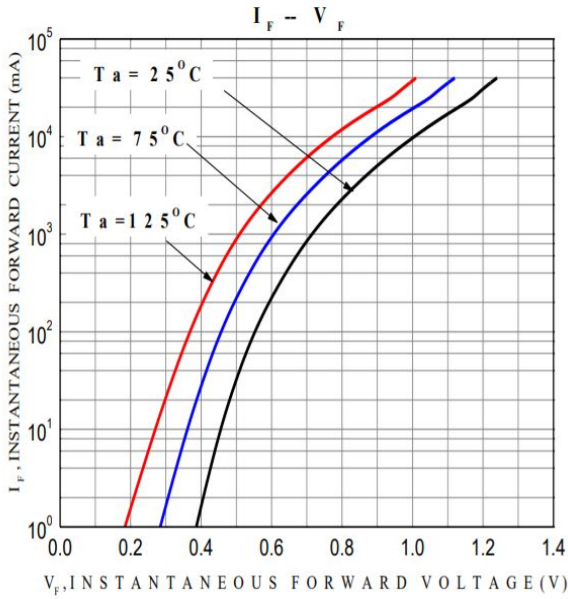


FIGURE 3. FORWARD CURRENT vs FORWARD VOLTAGE

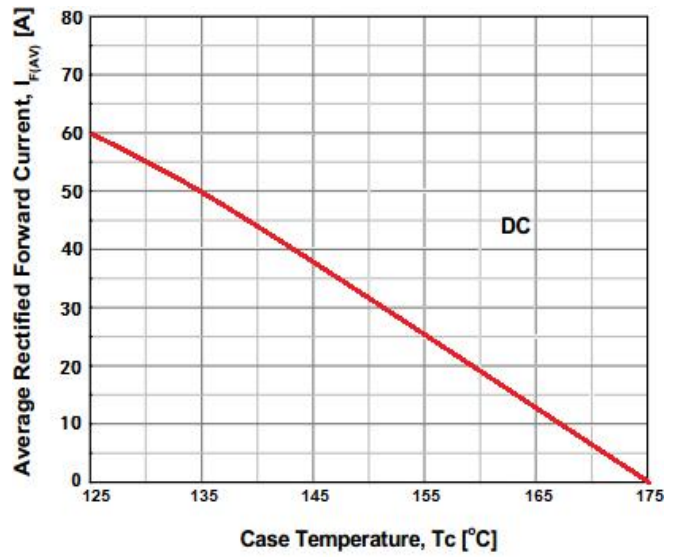


FIGURE 4. CURRENT DERATING CURVE

## 6 Typical Test Circuit and Waveform

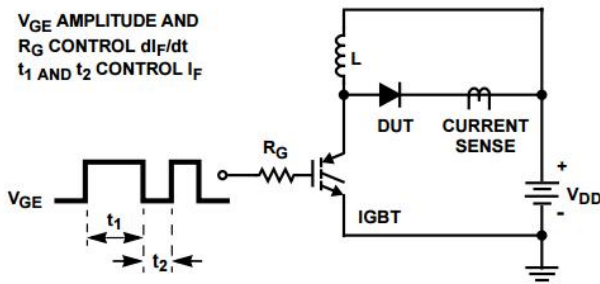


FIGURE 5. trr TEST CIRCUIT

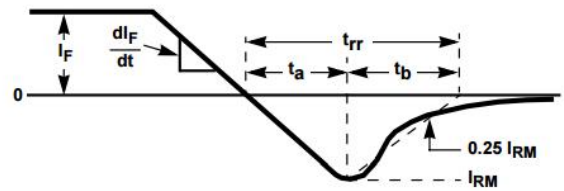


FIGURE 6. trr WAVEFORMS AND DEFINITIONS

$R < 0.1\Omega$   
 $E_{AVL} = 1/2LI^2 [V_{R(AVL)}/(V_{R(AVL)} - V_{DD})]$   
 $Q_1 = \text{IGBT } (BV_{CES} > \text{DUT } V_{R(AVL)})$

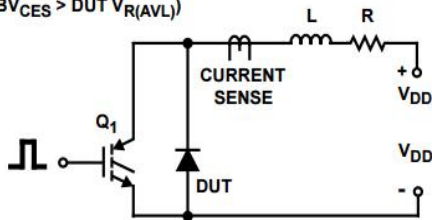


FIGURE 7. AVALANCHE ENERGY TEST CIRCUIT FIGURE

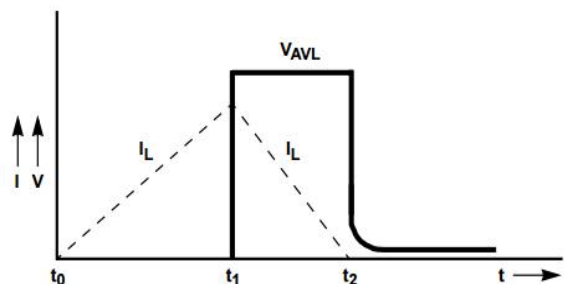
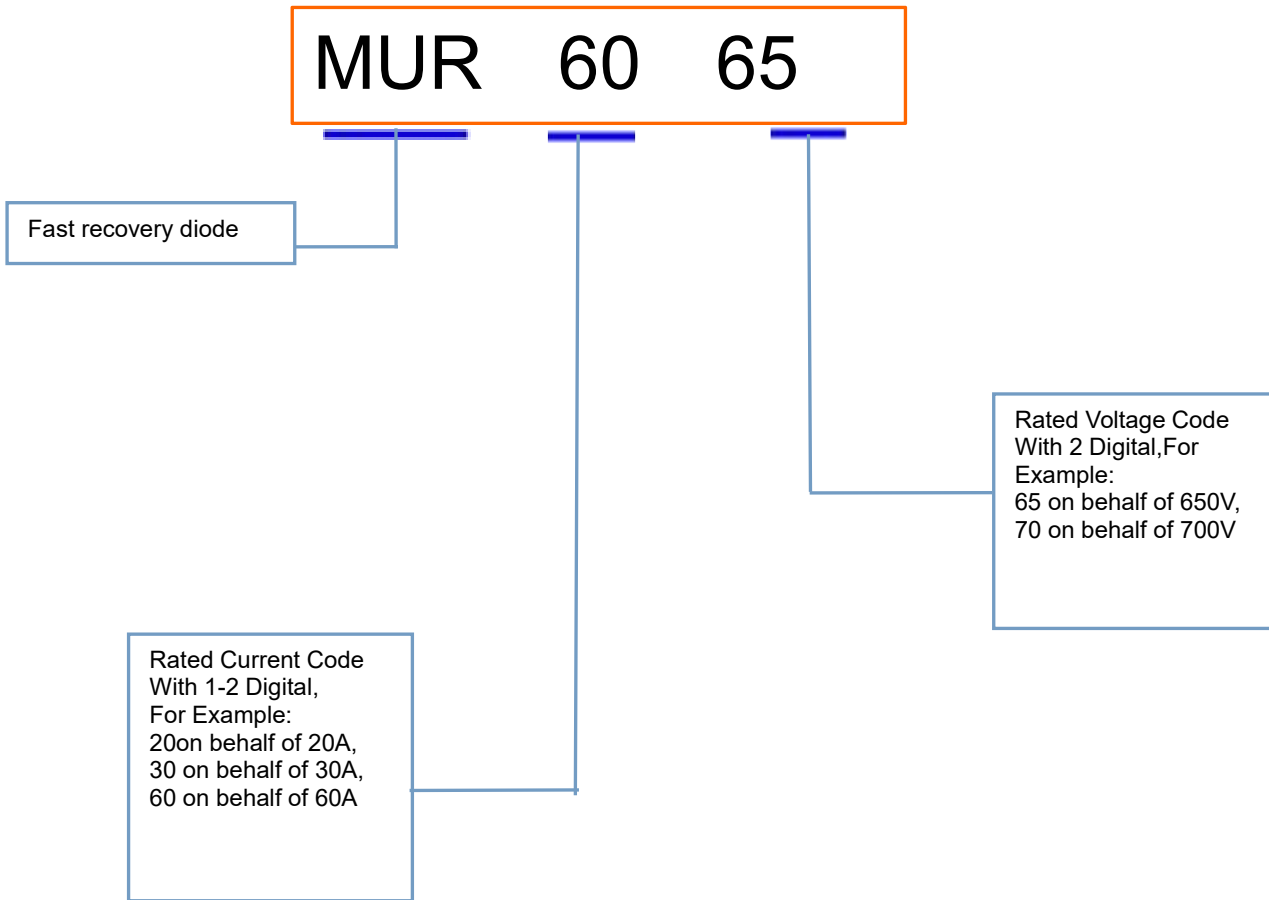


FIGURE 8. AVALANCHE CURRENT AND VOLTAGE WAVEFORMS

### 7 Product Names Rules

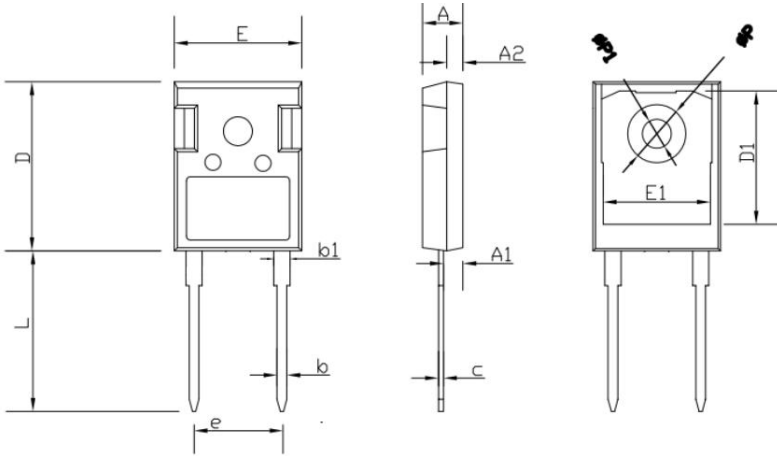


### 8 Product Specifications and Packaging Models

Product Model	Package Type	Mark Name	RoHS	Package	Quantity
MUR6065	TO-247-2L	MUR6065	Pb-free	Tube	300/box

## 9 Dimensions

### TO-247-2L PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	min.	max.	min.	max.
A	4.90	5.10	0.193	0.201
A1	2.31	2.51	0.091	0.099
A2	1.90	2.10	0.075	0.083
b	1.16	1.26	0.046	0.050
b1	1.96	2.06	0.0772	0.0812
c	0.59	0.66	0.0232	0.0260
D	20.90	21.10	0.8235	0.8313
D1	16.25	16.85	0.6403	0.6639
E	15.70	15.90	0.6186	0.6265
E1	13.10	13.50	0.5161	0.5319
e	10.88BCS			
L	19.80	20.10	0.7801	0.7919
ΦP	3.50	3.70	0.1379	0.1458
ΦP1	0	7.30	0	0.2876

## 10 Attentions

- Jiangsu Donghai Semiconductor Co.,Ltd. reserves the right to change the specification without prior notice! The customer should obtain the latest version of the information before making the order and verify that the information is complete and up to date.
- It is the responsibility of the purchaser for any failure or failure of any semiconductor product under certain conditions. It is the responsibility of the purchaser to comply with safety standards and to take safety measures in the system design and machine manufacturing of Jiangsu Donghai Semiconductor Co.,Ltd. products in order to avoid potential risk of failure. Injury or property damage.
- Product promotion is endless, our company will be dedicated to provide customers with better products.

## 10 Appendix

Revision history:

Date	REV.	Description	Page
2017.03.31	1.0	Original	
2022.01.01	1.1	Modify company name	all